

**Amendments to the Specification**

Please replace the paragraph at page 4, line 13 with the following amended paragraph:

FIG. 3b shows a cross section of gold deposited on the molybdenum; and

Please replace the paragraph at page 8, line 24 to page 9, line 2 with the following amended paragraph:

The third region 8a in the third resist layer 8 is then developed in a suitable resist developer, such as solution of 100% MIBK, for a suitable period of time, such as 360 seconds. This removes the resist in the third region 8a from the third resist layer 8, as shown in FIG. 2b, thereby forming a gate opening region 8b. Next, the second region 6a in the second resist layer 6 is developed in a suitable resist developer, such as a solution of one part Ethylene glycol monoethyl ether acetate (EGMEA): five parts Ethanol (ETHOETOH) for a suitable period of time, such as 45 to 70 seconds. This removes the resist in the second region 6a from the second resist layer 6, thereby forming a gate contact region 6b.